



# TSB82S200S(A)S-255A

## 10A/200V<sup>(1)</sup>, low VF Schottky barrier diode with trench MOS structure

### Mechanical Data

Chip Drawing	Item	Information	
	Die Size (A)	2082 $\mu\text{m}$	82 mil
	Top Metal Pad Size (B)	1950 $\mu\text{m}$	77mil
	Chip Size (C)	2002 $\mu\text{m}$	79mil
	Wafer Thickness (D)	255 $\mu\text{m}$	9.5 mil
	Scribe Line Width (E)	80 $\mu\text{m}$	3.15 mil
	Wafer Size	6 inch	
	Top Side Metallization	AL/Ag	
	Back Side Metallization	Ti Ni Ag	
	Recommended Storage Environment	Stored in original container, in dry nitrogen, (6 months at an ambient temperature of 23°C $\pm$ 3°C)	

### Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise specified)<sup>(2)</sup>

Parameter	Description	Min.	Typ.	Max.	Unit	Test Condition
$V_{BR}$	Reverse Breakdown Voltage	210	230	-	V	$I_R = 100\mu\text{A}$
$V_F$	Instantaneous Forward Voltage	-	0.83	0.88	V	$I_F = 10\text{A}^{(3)}$
$I_R$	Reverse Leakage Current	-	0.5	10	$\mu\text{A}$	$V_R = 200\text{V}$
$T_J, T_{STG}$	Operating and Storage Temperature	-40°C to 150°C Max				

#### Note:

(1) The preliminary wafer datasheet only for reference;

(2) This characteristics assume the dies are assembled in SMC packages. Actual performance may degrade when assembled. YJ does not guarantee device performance after assembly;

(3) Pulse Width  $t_p = < 300\mu\text{s}$ , Duty Cycle  $< 2\%$ ;